

REMARKS

Claims 1, 3-6, 13, 17, 23, 26, 27, 32, 33, 36 and 39 are amended. Claims 1-39 are in the application for consideration.

All of the Examiner's 35 USC §112 rejections have been addressed by amendment to the claims specifically referred to by the Examiner. The amendments made either insert the language requested by the Examiner, or delete certain language which was objected to. Further, other claims have been amended to be consistent with the amendments made to the claims which were formally rejected under 35 USC §112. Accordingly, all of the indefiniteness rejections raised by the Examiner have been dealt with by amendment to the affected claims, and withdrawal of these rejections is requested.

The undersigned appreciates the Examiner's indicated allowability of the subject matter of claims 1-12. In light of the amendments to claims 1, and 3-6 to address the above §112 issues, claims 1-12 should now summarily be formally allowed. Action to that end is requested.

Independent claims 13 and 17 stand rejected as being anticipated by Yagashita et al. Such claims have been amended to recite that the isolation trench is formed within semiconductive material of a semiconductor substrate, and that the

semiconductive material has an outer surface. Claims 13 and 17 are further amended to recite the removing of trench isolation material from within that isolation trench within semiconductive material to form a line trench having a base which is lower than the outer surface of the semiconductive material. Such is neither shown nor suggested by Yagashita et al.

Specifically, it is not believed that Yagashita et al. discloses a local interconnect. Regardless, Yagashita's removal of trench isolation material to form trench 17 does not remove trench isolation material from within the isolation trench received below the outermost surface of its semiconductive material 11. Accordingly, the trench 17 formed in Yagashita et al. has a base which is received at or higher than the outer surface of its material 11. Accordingly, Applicant's independent claims 13 and 17 clearly recite something which is neither shown nor suggested by Yagashita et al., and such claims should be allowed. Action to that end is requested.

Independent claim 23 stands rejected as being anticipated by Yagashita et al. Claim 23 has been amended in like manner to that asserted above with respect to claims 13 and 17. Accordingly, claim 23 recites something which is neither shown nor suggested in Yagashita et al., and this rejection should be withdrawn. Action to that end is requested.

Independent claims 23 and 27 also stand rejected as being anticipated by Kim and Ochii. Such claims have also been amended to recite that after forming the conductive material, insulative material is formed within the line trench below the outer surface of the semiconductive material. Clearly, no such material is formed in any of the allegedly equivalent trenches in Kim or Ochii as applied by the Examiner. Accordingly, independent claims 23 and 27 respectively recite something which is neither shown nor suggested by Kim or Ochii, and the rejection should be withdrawn. Action to that end is requested.

Independent claim 32 stands rejected as being anticipated by Yagashita et al. Claim 32 has been amended to recite that the line trench is etched into a desired line configuration into trench isolation material formed relative to an outer surface of semiconductive material of a semiconductor substrate. Further, the line trench is recited as having a base which is lower than the outer surface of the semiconductive material. For essentially the same reasons as argued above with respect to claims 13 and 17, Yagashita et al. does not disclose this particular attribute of claim 32. Accordingly, the rejection of claim 32 should be withdrawn, and action to that end is requested.

Independent claims 32 and 36 stand rejected as being anticipated by or obvious over Ochii. Each such claim has been amended to recite that the line trench has an

insulative base. This line trench and insulative base are further recited to be formed by etching into trench isolation material. Ochiai neither discloses nor suggests such. Specifically, the undersigned interprets the Examiner to be asserting that the two trenches illustrated in Figs. 3A-3D are "line trenches" in the context of Applicant's claims. However, the only etching of the allegedly equivalent isolation material 26 occurs in the processing going from Figs. 3A to 3B. The Examiner will note that no etching is being conducted of material 26 within the right illustrated isolation trench as it is protected by photoresist 27. Accordingly, the "etching" action of Applicant's independent claims 32 and 36 is not met by the etching action in Ochiai with respect to the Figs. 3A, 3B right illustrated trench.

With respect to the Figs. 3A, 3B left illustrated trench, the etching action of material 26 results in the trench having a p-type substrate material base, and thereby does not form a line trench having an insulative base as Applicant now more positively recites in independent claims 32 and 36. Accordingly, such claims now recite something which is not shown, nor suggested, by Ochiai. Accordingly, withdrawal of this rejection is warranted, and requested.

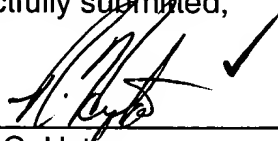
Applicant's dependent claims should be allowed as depending from allowable base claims, as well as for their own recited features which are neither shown nor suggested in the cited art. Further, and by way of example only, the additionally cited

Wolf et al., Huang and Kim references do not overcome the deficiencies argued above with respect to the other references, nor in combination with any reference suggest the claims as amended herein.

Having addressed all of the issues raised by the Examiner in the last Action, this application is believed to be in immediate condition for allowance, and action to that end is requested.

Respectfully submitted,

Dated: 2/18/03

By: 
Robert C. Hyta
Reg. No. 46,791

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